FCPF850N80Z

N-Channel SuperFET® II MOSFET

800 V, 8 A, 850 mΩ

Features

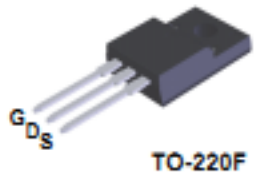
- Typ. $R_{DS(on)}$ = 710 mΩ (Typ.)
- Ultra Low Gate Charge (Typ. Q_g = 22 nC)
- Low E_{oss} (Typ. 2.3 uJ @ 400V)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 108 pF)
- 100% Avalanche Tested
- RoHS Compliant
- ESD Improved Capability

Applications

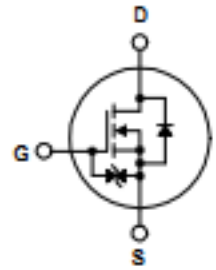
- AC - DC Power Supply
- LED Lighting

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. In addition, internal gate-source ESD diode allows to withstand over 2kV HBM surge stress. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as Audio, Laptop adapter, Lighting, ATX power and industrial power applications.



TO-220F



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FCPF850N80Z	Unit
V_{DSS}	Drain to Source Voltage		800	V
V_{GSS}	Gate to Source Voltage	- DC	±20	V
		- AC (f > 1 Hz)	±30	
I_D	Drain Current	- Continuous (T_C = 25°C)	8.0*	A
		- Continuous (T_C = 100°C)	5.1*	
I_{DM}	Drain Current	- Pulsed (Note 1)	18*	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	114	mJ
I_{AR}	Avalanche Current	(Note 1)	1.2	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	0.284	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt	(Note 3)	20	
P_D	Power Dissipation	(T_C = 25°C)	28.4	W
		- Derate Above 25°C	0.24	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature, with heatsink.

Thermal Characteristics

Symbol	Parameter	FCPF850N80Z	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF850N80Z	FCPF850N80Z	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	800	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C	-	0.8	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800 V, V_{GS} = 0 V	-	-	25	µA
		V_{DS} = 640 V, V_{GS} = 0 V, T_C = 125°C	-	-	250	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±10	µA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.6 mA	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 3 A	-	710	850	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 3 A	-	3.5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	-	990	1315	pF
C_{oss}	Output Capacitance		-	28	37	pF
C_{rss}	Reverse Transfer Capacitance		-	0.74	-	pF
C_{oss}	Output Capacitance	V_{DS} = 480 V, V_{GS} = 0 V, f = 1 MHz	-	15	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	108	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 640 V, I_D = 6 A, V_{GS} = 10 V (Note 4)	-	22	29	nC
Q_{gs}	Gate to Source Gate Charge		-	5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	8.6	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	2.4	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 6 A, V_{GS} = 10 V, R_g = 4.7 Ω (Note 4)	-	18	42	ns
t_r	Turn-On Rise Time		-	10	30	ns
$t_{d(off)}$	Turn-Off Delay Time		-	40	90	ns
t_f	Turn-Off Fall Time		-	4.5	19	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	18	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 6 A	-	-	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 6 A, dI_F/dt = 100 A/µs	-	318	-	ns
Q_{rr}	Reverse Recovery Charge		-	4.5	-	µC

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. I_{AS} = 1.2 A, V_{DD} = 50 V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 8 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially independent of operating temperature typical characteristics.